

Erratum: “Nonvolatile and unipolar resistive switching characteristics of pulsed laser ablated NiO films” [J. Appl. Phys. 108, 104513 (2010)]

Cite as: J. Appl. Phys. 109, 119902 (2011); <https://doi.org/10.1063/1.3596515>

Submitted: 25 April 2011 • Accepted: 05 May 2011 • Published Online: 10 June 2011

D. Panda, A. Dhar and S. K. Ray



[View Online](#)



[Export Citation](#)

ARTICLES YOU MAY BE INTERESTED IN

[Nonvolatile and unipolar resistive switching characteristics of pulsed laser ablated NiO films](#)
Journal of Applied Physics 108, 104513 (2010); <https://doi.org/10.1063/1.3514036>

Lock-in Amplifiers
up to 600 MHz



Zurich
Instruments



Erratum: “Nonvolatile and unipolar resistive switching characteristics of pulsed laser ablated NiO films” [J. Appl. Phys. 108, 104513 (2010)]

D. Panda, A. Dhar, and S. K. Ray^{a)}

Department of Physics and Meteorology, Indian Institute of Technology Kharagpur, Kharagpur, India, 721 302

(Received 25 April 2011; accepted 5 May 2011; published online 10 June 2011)

[doi:10.1063/1.3596515]

In the original published version of this article, Eq. (1) and the unit of the x-axis in Fig. 9(a) are incorrect. The rectified equation and figure are given below.

$$\ln(J/E) \sim -q\phi_b - \left(\frac{\sqrt{q^3/\pi\epsilon_r\epsilon_0}}{\lambda k_B T} \cdot \sqrt{E} \right) \quad (1)$$

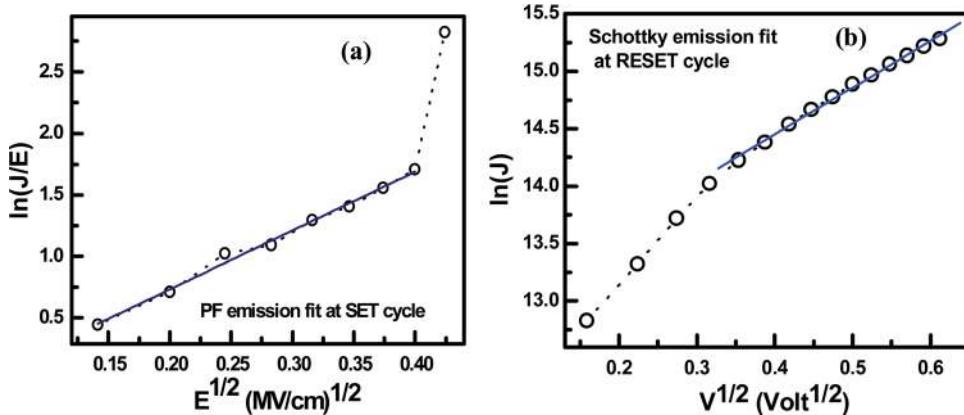


FIG. 9. (Color online) Curve fitting plots for applying (a) Schottky (LRS) and (b) Poole-Frenkel (HRS) emissions of the I-V characteristics presented in Fig. 8(a).

^{a)}Author to whom correspondence should be addressed. Electronic addresses: dpanda@phy.iitkgp.ernet.in; physkr@phy.iitkgp.ernet.in.